

**HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODE****MAIN PRODUCT CHARACTERISTICS**

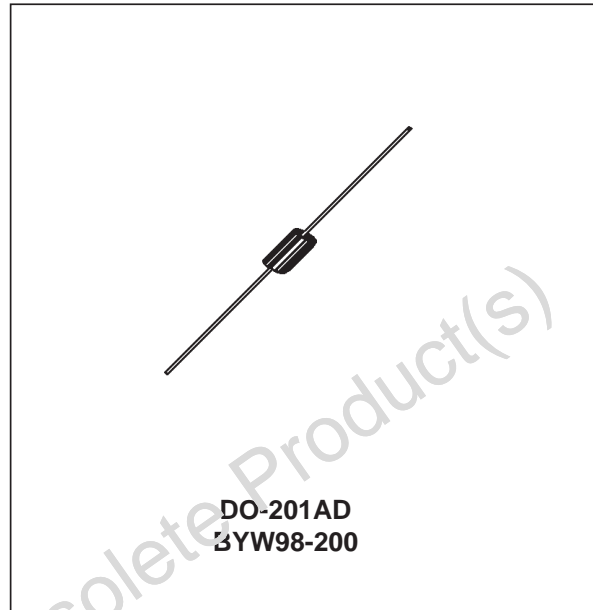
I_{F(AV)}	3A
V_{RRM}	200 V
T_j (max)	150 °C
V_F (max)	0.85 V
trr (max)	35 ns

FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times

DESCRIPTION

Low voltage drop and rectifier suited for switching mode base drive and transistor circuits.

**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	200	V
I _{FRM}	Repetitive peak forward current*	tp = 5μs F = 1KHz	110 A
I _{F(AV)}	Average forward current	Ta = 75°C δ = 0.5	3 A
I _{FSM}	Surge non repetitive forward current	tp = 10ms Sinusoidal	70 A
T _{stg}	Storage temperature range	- 65 to + 150	°C
T _j	Maximum operating junction temperature	150	°C
T _L	Maximum lead temperature for soldering during 10s at 4mm from case	230	°C

* On infinite heatsink with 10mm lead length.

THERMAL PARAMETERS

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction-ambient*	25	°C/W

* On infinite heatsink with 10mm lead length.

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _R RM			10	μA
		T _j = 100°C				0.5	mA
V _F **	Forward voltage drop	T _j = 25°C	I _F = 9A			1.2	V
		T _j = 100°C	I _F = 3A		0.78	0.85	

Pulse test : * tp = 5 ms, δ < 2 %

** tp = 380 μs, δ < 2 %

To evaluate the maximum conduction losses use the following equations:

$$P = 0.75 \times I_{F(AV)} + 0.04 I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Test conditions		Min.	Typ.	Max.	Unit
trr	I _F = 1A	dI _F /dt = - 50A/μs V _R = 30V	T _j = 25°C		35	ns
Qrr	I _F = 3A	dI _F /dt = - 20A/μs V _R ≤ 30V	T _j = 25°C	15		nC
tfr	I _F = 3A	dI _F /dt = - 50A/μs Measured at 1.1 x V _F max	T _j = 25°C	20		ns
V _{FP}	I _F = 3A	dI _F /dt = - 50A/μs	T _j = 25°C	5		V

Fig. 1: Average forward power dissipation versus average forward current.

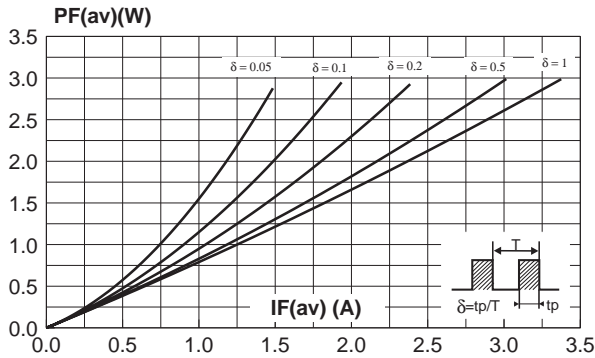


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

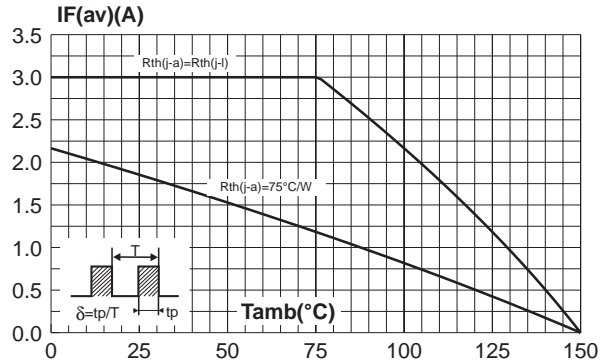


Fig. 3: Thermal resistance versus lead length.

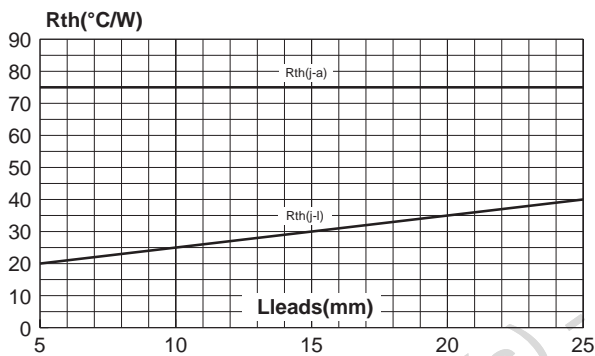


Fig. 4: Variation of thermal impedance junction to ambient versus pulse duration (recommended pad layout, epoxy FR4, $e(\text{Cu}) = 35\mu\text{m}$).

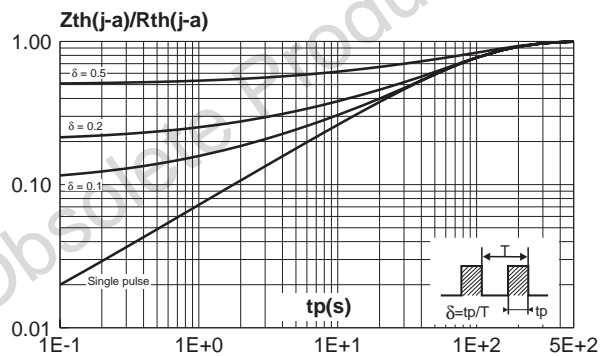


Fig. 5: Forward voltage drop versus forward current (maximum values).

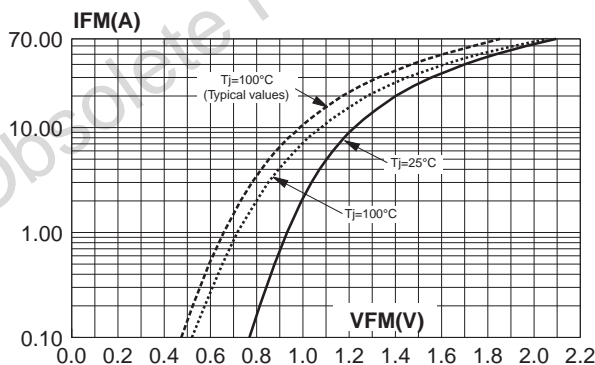


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

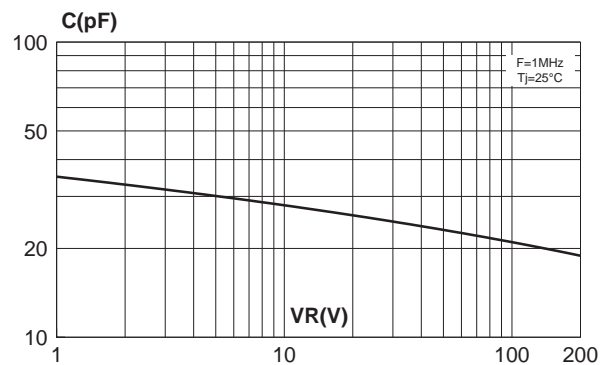


Fig. 7: Reverse recovery time versus di_F/dt .

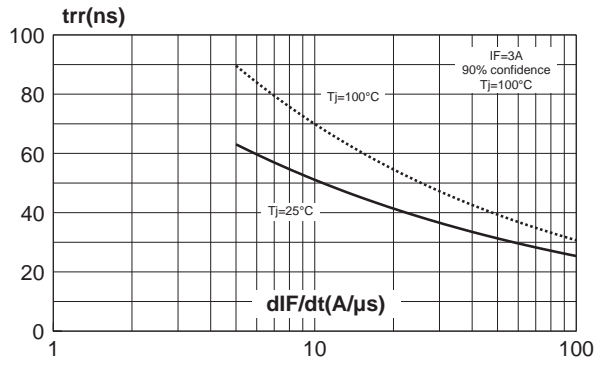


Fig. 8: Peak reverse recovery current versus di_F/dt .

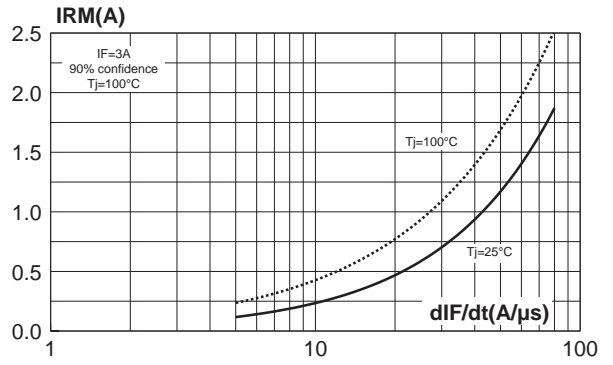
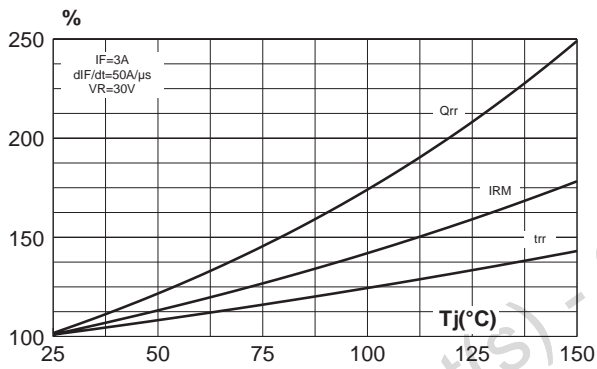


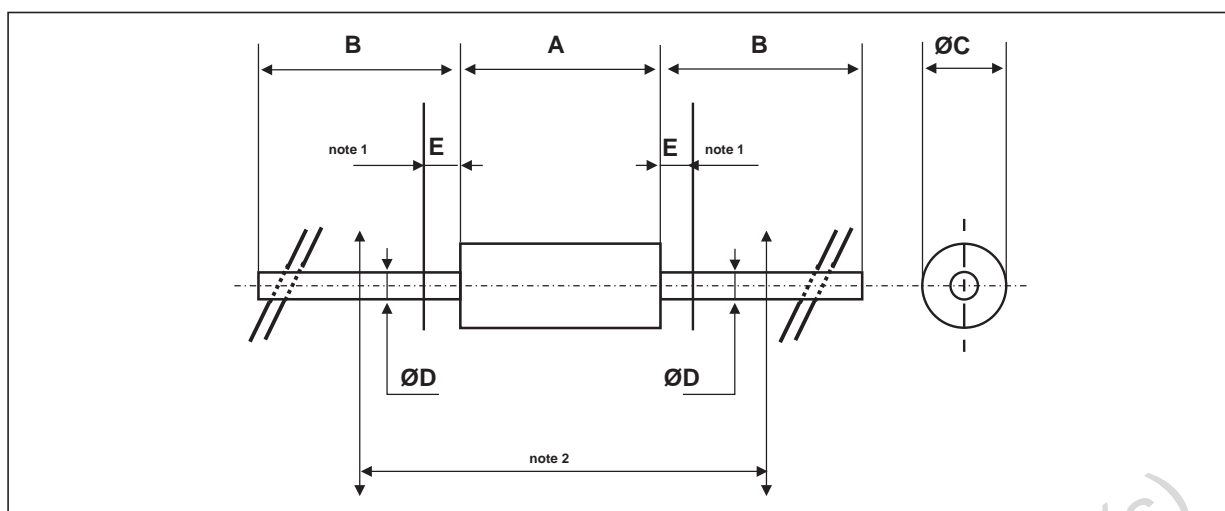
Fig. 9: Dynamic parameters versus junction temperature.



Obsolete Product(s)

PACKAGE MECHANICAL DATA

DO-201AD



REF.	DIMENSIONS				NOTES
	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
A		9.50		0.374	1 - The lead diameter $\varnothing D$ is not controlled over zone E 2 - The minimum axial length within which the device may be placed with its leads bent at right angles is 0.59" (15 mm)
B	25.40		1.000		
$\varnothing C$		5.30		0.209	
$\varnothing D$		1.30		0.051	
E		1.25		0.049	

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
BYW98-200	BYW98-200	DO-201AD	1.16 g	600	Ammopack
BYW98-200RL	BYW98-200	DO-201AD	1.16 g	1900	Tape and reel

- White band indicates cathode
- Epoxy meets UL94,V0

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